

# NDNM01021

## 9.0-10.0GHz GaN Internally Matched HEMT

### ► Features

- Internally Matched GaN HEMT
- Frequency range: 9.0-10.0 GHz
- Output Power: 100W (Typ.)
- Gain: 7dB
- PAE: 37% (Typ.)
- Bias: 28V/-3V
- Hermetically Sealed Package



### ► General Description

NDNM01021 is a GaN-HEMT that is internally matched for 9.0-10.0GHz with high power and efficiency. The transistor provides 100W output power, 7dB gain and 37% power add efficiency at 28V.

### ► Absolute Maximum Ratings (TA=25 °C)

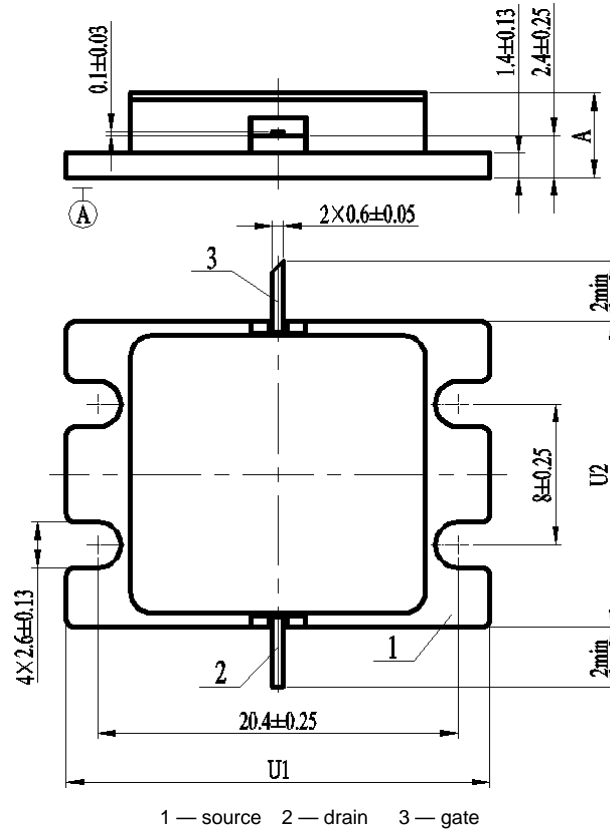
Symbol	Parameter	Value	Notes
V <sub>ds</sub>	Drain Bias Voltage	32V	
V <sub>gs</sub>	Gate Bias Voltage	-5V	
T <sub>ch</sub>	Channel Temperature	175°C	
T <sub>stg</sub>	Storage Temperature	-55~175°C	

Any of the stresses above the listed ratings may cause permanent damage.

► **Specifications** ( $T_A=25\text{ }^\circ\text{C}$ )

Symbol	Parameter	Conditions	Value			Units
			Min	Typical	Max	
$P_{out}$	Output Power	Vd=28V, Vg=-3V F: 9.0-10.0GHz		50	-	dBm
$G_p$	Power Gain		-	7	-	dB
$\eta_{add}$	Power Added Efficiency		-	37	-	%
$\Delta G_p$	Gain Flatness		-0.8	-	+0.8	dB

► **Package size**

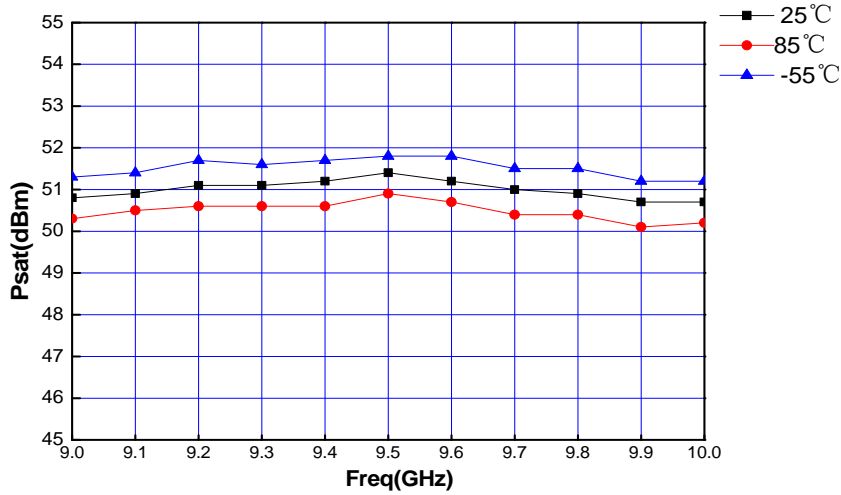


Unit: mm

Symbol	Value	
	Min	Max
U1	23.80	24.20
U2	17.20	17.60
A	-	5.2

► Typical Performances ( $T_A=25\text{ }^\circ\text{C}$ )

Output Power



Power Added Efficiency (PAE)

